









SN74AHC32Q-Q1

SGDS019D - FEBRUARY 2002 - REVISED FEBRUARY 2024

SN74AHC32Q-Q1 Automotive Quadruple 2-Input Positive-OR Gates

1 Features

- Qualified for automotive applications
- Operating range 2V to 5.5V V_{CC}
- Low power consumption, 10µA maximum I_{CC}
- ±8mA output drive at 5V
- Latch-up performance exceeds 250mA per JESD 17

2 Applications

- Enable or disable a digital signal
- Controlling an indicator LED
- Translation between communication modules and system controllers

3 Description

The SN74AHC32Q-Q1 devices are quadruple 2input positive-OR gates. These devices perform the Boolean function $Y = \overline{A \times B}$ or Y = A + B in positive logic.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE(3)
	BQA (WQFN, 14)	3mm × 2.5mm	3mm × 2.5mm
SN74AHC32Q-Q1	PW (TSSOP, 14)	5mm × 6.4mm	5mm × 4.4mm
	D (SOIC, 14)	8.7mm × 6mm	8.7mm × 3.9mm

- (1) For more information, see Section 11.
- The package size (length × width) is a nominal value and (2) includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.



Logic Diagram (Positive Logic)



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4 Pin Configuration and Functions

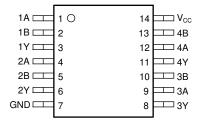


Figure 4-1. SN74AHC32 D or PW Package, 14-Pin (Top View)

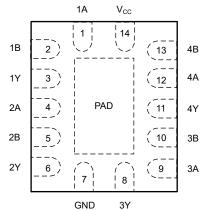


Figure 4-2. SN74AHC32 BQA Package, 14-Pin (Top View)

Table 4-1. Pin Functions

	PIN	TVDE(1)	DESCRIPTION		
NAME	PIN No.	TYPE ⁽¹⁾	DESCRIPTION		
1A	1	I	1A Input		
1B	2	I	1B Input		
1Y	3	0	1Y Output		
2A	4	I	2A Input		
2B	5	I	2B Input		
2Y	6	0	2Y Output		
3A	9	I	3A Input		
3B	10	I	3B Input		
3Y	8	0	3Y Output		
4A	12	I	4A Input		
4B	13	I	4B Input		
4Y	11	0	4Y Output		
GND	7	_	Ground Pin		
V _{CC}	14	_	Power Pin		
Thermal Pad ⁽²⁾	-	-	Thermal Pad		

⁽¹⁾ Signal Types: I = Input, O = Output, I/O = Input or Output.

⁽¹⁾ Signal Types: I = Inp(2) BQA Package Only

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
V _I (2)	Input voltage		-0.5	7	V
V _O ⁽²⁾	Output voltage		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	(V ₁ < 0)		-20	mA
I _{OK}	Output clamp current	$(V_O < 0 \text{ or } V_O > V_{CC})$		±20	mA
Io	Continuous output current	$(V_O = 0 \text{ to } V_{CC})$		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	V
V (ESD)	Electrostatic discharge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	V

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

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⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.



5.3 Recommended Operating Conditions

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
		V _{CC} = 2 V	1.5		
V_{IH}	High-level input voltage ⁽¹⁾	V _{CC} = 3V	2.1		V
		V _{CC} = 5.5 V	3.85		
		V _{CC} = 2 V		0.5	
V_{IL}	Low-level Input voltage ⁽¹⁾	V _{CC} = 3 V		0.9	V
		V _{CC} = 5.5 V		1.65	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 2 V		-50	μA
он	High-level output current	V_{CC} = 3.3 V ± 0.3 V		-4	A
		V _{CC} = 5 V ± 0.5 V		-8	mA
		V _{CC} = 2 V		50	μA
OL	Low-level output current	V_{CC} = 3.3 V ± 0.3 V		4	Λ
		V _{CC} = 5 V ± 0.5 V		8	mA
۸4/۸	lumit Transition vice and all rate	V _{CC} = 3.3 V ± 0.3 V		100	A /
Δt/Δv	Input Transition rise or fall rate	V _{CC} = 5 V ± 0.5 V		20	ns/V
T _A	Operating free-air temperature	,	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5.4 Thermal Information

			SN74AHC32Q-Q1		
THERMAL METRIC(1)		D	PW	BQA	UNIT
		14	14	14	
R _{0JA}	Junction-to-ambient thermal resistance	124.6	147.7	88.3	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V.	TA	= 25°C				NIT	
PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	MIN	MAX	INII	
		2 V	1.9	2		1.9			
	I _{OH} = -50 μA	3 V	2.9	3		2.9			
V _{OH}		4.5 V	4.4	4.5		4.4		V	
	I _{OH} = -4 mA	3 V	2.58			2.48			
	I _{OH} = -8 mA	4.5 V	3.94			3.8			
		2 V			0.1		0.1		
	I _{OL} = 50 μA	3 V			0.1		0.1		
V _{OL}		4.5 V			0.1		0.1	V	
	I _{OH} = 4 mA	3 V			0.36		0.5		
	I _{OH} = 8 mA	4.5 V			0.36		0.5		
l _l	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	μΑ	
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20	μA	
Ci	V _I = V _{CC} or GND	5 V		2	10			pF	

5.6 Switching Characteristics, V_{CC} = 3.3 V \pm 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

PARAMETER	FROM	то	LOAD	T _A = 25	°C	T _A = -40°C	TO 125°C	UNIT
FARAMETER	PARAMETER (INPUT) (OL	(OUTPUT)	(OUTPUT) CAPACITANCE		MAX	MIN	MAX	ONII
t _{PLH}	A or B	V	C ₁ = 15 pF	5.5	7.9	1	9.5	ns
t _{PHL}	AOID	T	Ο[– 13 μι	5.5	7.9	1	9.5	115
t _{PLH}	A or B		C _L = 50 pF	8	11.4	1	13	ns
t _{PHL}	AOID	'	О[– 30 рі	8	11.4	1	13	115

5.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range(unless otherwise noted) (see Figure 6-1)

PARAMETER	FROM	то	LOAD	T _A = 25	°C	T _A = -40°C	ΓΟ 125°C	UNIT
FARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	TYP	MAX	MIN	MAX	ONIT
t _{PLH}	A or B	V	C _L = 15 pF	3.8	5.5	1	6.5	ns
t _{PHL}	AOIB	I	C _L = 15 βi	3.8	5.5	1	6.5	115
t _{PLH}	A or B	Y C _L = 50	C = 50 pE	5.3	7.5	1	8.5	no
t _{PHL}	AOIB		CL = 30 pr	5.3	7.5	1	8.5	ns

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5.8 Noise Characteristics

 $V_{CC} = 5 \text{ V}, C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}^{(1)}$

	PARAMETER	MIN	TYP	MAX	UNIT
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.3	0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.3	-0.8	V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		4.7		V
V _{IH(D)}	High-level dynamic input voltage	3.5			V
V _{IL(D)}	Low-level dynamic input voltage			1.5	V

(1) Characteristics are for surface-mount packages only.

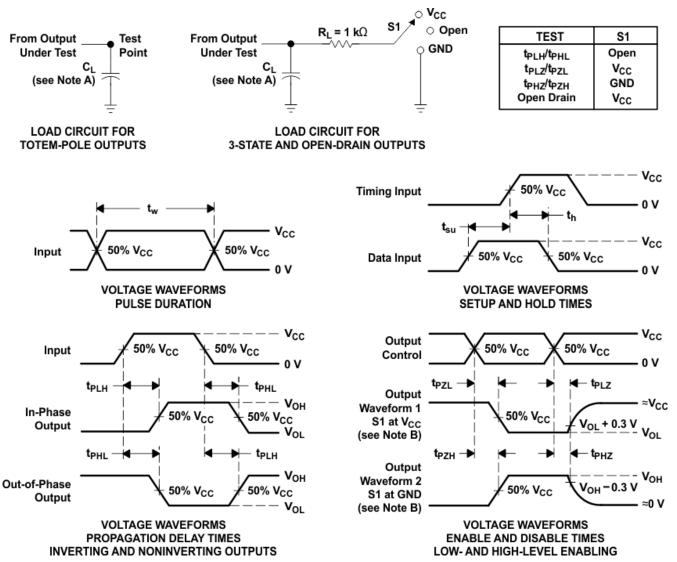
5.9 Operating Characteristics

 $V_{CC} = 5 \text{ V}, T_{A} = 25^{\circ}\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load, f = 1 MHz	14	pF



6 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

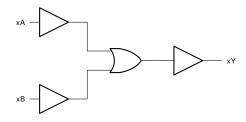
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7 Detailed Description

7.1 Overview

The SN74AHC32Q-Q1 contains four independent 2-input OR Gates. Each gate performs the Boolean function Y = A + B in positive logic.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a $10\text{-k}\Omega$ resistor, however, is recommended and will typically meet all requirements.

7.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

7.3.3 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as shown in Figure 7-1.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

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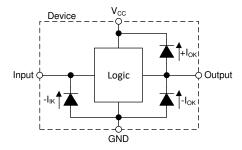


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74AHC32Q-Q1.

Table 7-1. Function Table

INPU	ITS ⁽¹⁾	ОИТРИТ
Α	В	Y
Н	Н	Н
L	Н	Н
Н	L	Н
L	L	L

(1) H = high voltage level, L = low voltage level, X = do not care, Z = high impedance

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

In this application, three 2-input OR gates are combined to produce a 4-input OR gate function as shown in Figure 8-1. The fourth gate can be used for another application in the system, or the inputs can be grounded and the channel left unused.

The SN74AHC32Q-Q1 is used to directly control the Enable pin of a fan driver. The fan driver requires only one input signal to be HIGH before being enabled, and should be disabled in the event that all signals go LOW. The 4-input OR gate function combines the four individual overheat signals into a single active-high enable signal.

Temperature sensors can often be spread throughout a system rather than being in a centralized location. This would mean longer length traces or wires to pass signals through leading to slower edge transitions. This makes the SN74AHC32Q-Q1 useful for combining the incoming signals.

8.2 Typical Application

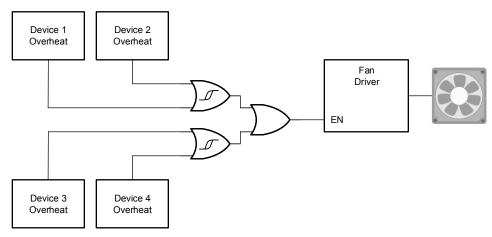


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AHC32Q-Q1 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHC32Q-Q1 plus the maximum supply current, I_{CC}, listed in the Electrical Characteristics, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the Absolute Maximum Ratings.

The SN74AHC32Q-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74AHC32Q-Q1 can drive a load with total resistance described by $R_L \ge V_O / I_O$, with the output voltage and current defined in the Electrical Characteristics table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation application note.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application note.

CAUTION

The maximum junction temperature, T_{J(max)} listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Absolute Maximum Ratings. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the Absolute Maximum Ratings.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHC32Q-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74AHC32Q-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the Recommended Operating Conditions table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the VOH specification in the Electrical Characteristics. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OI} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.

Product Folder Links: SN74AHC32Q-Q1

8.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHC32Q-Q1 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

8.2.3 Application Curves

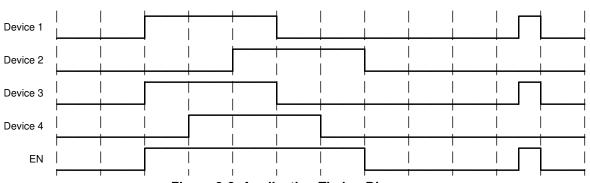


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Layout Example*.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or $V_{\rm CC}$, whichever makes more sense for the logic function or is more convenient.



8.4.2 Layout Example

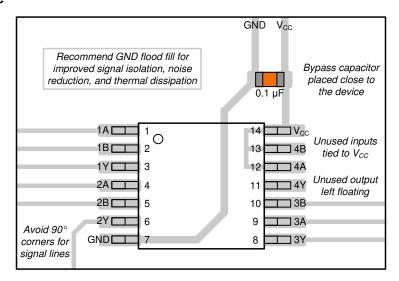


Figure 8-3. Example Layout for the SN74AHC32Q-Q1

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support (Analog)

9.1.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 9-1. Related Links

PARTS	PRODUCT FOLDER	ODUCT FOLDER SAMPLE & BUY TECHNICAL DOCUMENTS		TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74AHC32Q-Q1	Click here	Click here	Click here	Click here	Click here

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

	Changes from Revision C (October 2023) to Revision D (February 2024)	Page
•	Updated RθJA values: D = 86 to 124.6, all values in °C/W	5

Changes from Revision B (June 2023) to Revision C (October 2023)

mana from Baylaian C (October 2022) to Baylaian B (Fabruary 2024)

Page



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC32QDRG4Q1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC32Q	Samples
SN74AHC32QDRQ1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC32Q	Samples
SN74AHC32QPWRG4Q1	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA32Q	Samples
SN74AHC32QPWRQ1	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA32Q	Samples
SN74AHC32QWBQARQ1	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC32Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

www.ti.com 9-Apr-2024

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PACKAGE MATERIALS INFORMATION

www.ti.com 25-Jan-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC32QPWRG4Q1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHC32QPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHC32QWBQARQ1	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC32QPWRG4Q1	TSSOP	PW	14	2000	367.0	367.0	35.0
SN74AHC32QPWRQ1	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74AHC32QWBQARQ1	WQFN	BQA	14	3000	210.0	185.0	35.0

2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

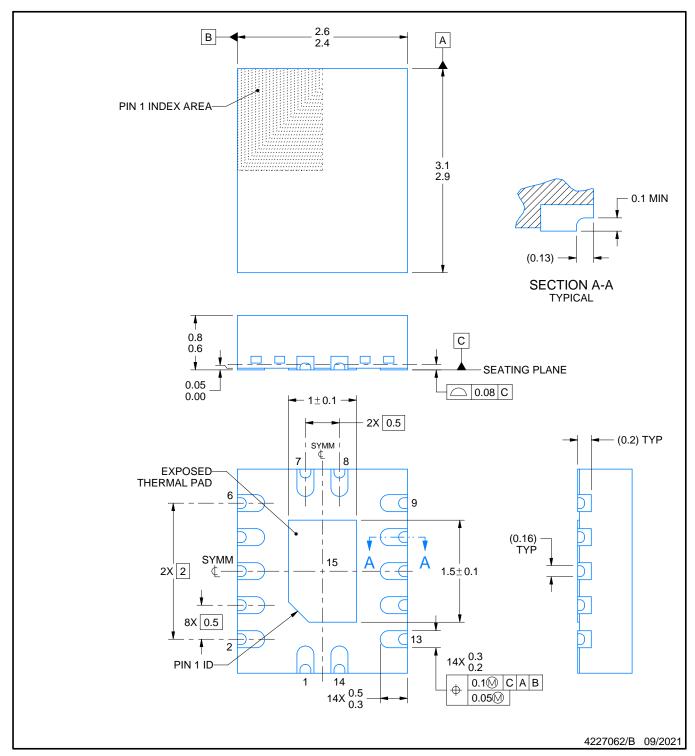
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



INSTRUMENTS www.ti.com



PLASTIC QUAD FLATPACK - NO LEAD

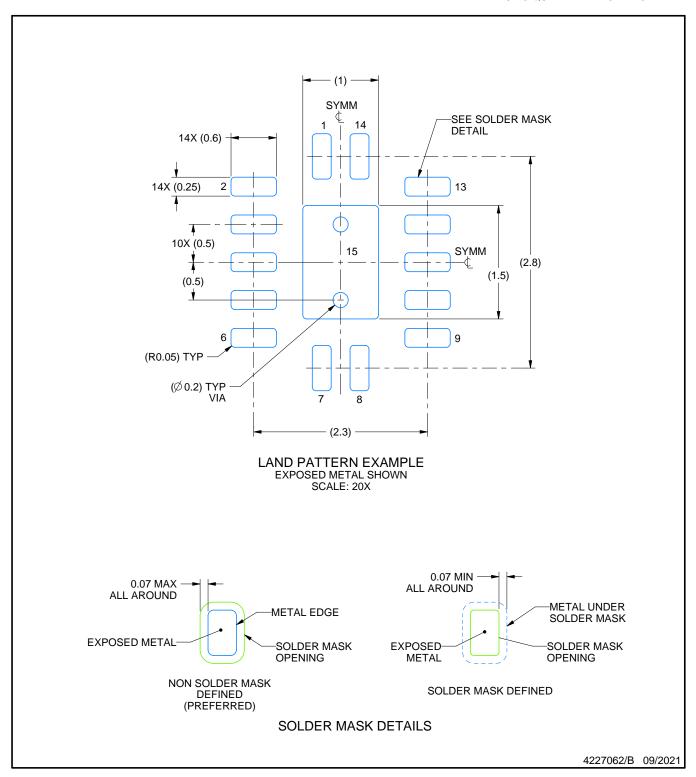


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

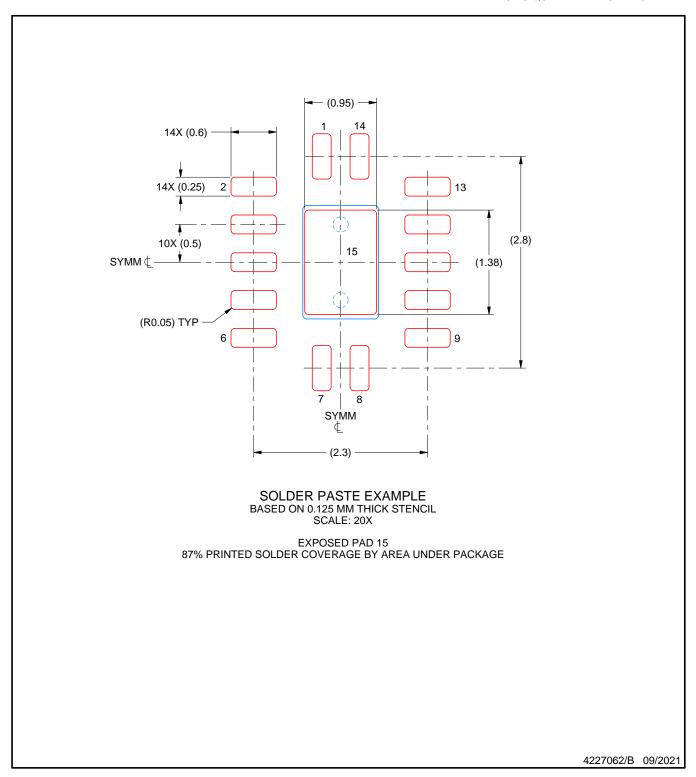


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
 - Sody length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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